CDC930

133-MHz DIFFERENTIAL CLOCK SYNTHESIZER/DRIVER FOR PC MOTHERBOARDS WITH 3-STATE OUTPUTS

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- Generates Clocks for Pentium®4 **Microprocessors**
- Uses a 14.318 MHz Crystal Input to **Generate Multiple Output Frequencies**
- Includes Spread Spectrum Clocking (SSC), 0.6% Downspread for Reduced EMI With Theoretical EMI Damping of 7 dB[†]
- **Power Management Control Terminals**
- Low Output Skew and Jitter for Clock Distribution
- **Operates From Single 3.3-V Supply**
- Consumes Less Than 30-mA Power-Down Current
- **Generates the Following Clocks:**
 - 4 HCLK (Host) (Different Pairs-100/133 MHz)
 - 1 3VMREF Pair (3.3 V, 180° Shifted 50/66 MHz)
 - 10 PCI (3.3 V, 33.3 MHz)
 - 2 REF (3.3 V, 14.318 MHz)
 - 4 3V66 MHz (3.3 V, 66 MHz)
 - 2 3V48 MHz (3.3 V, 48 MHz)
- Packaged in 56-Pin SSOP Package

description

The CDC930 is a differential clock synthesizer/ driver that generates HCLK/HCLK, 3VMREF/ 3VMREF, PCI, 3V66, 3V48, REF system clock signals to support a computer system with a Pentium®4 microprocessor and a Direct Rambus™ memory subsystem.

GND 56 V_{DD}3.3V REF0/MultSel0 [55 ☐ 3VMREF 2 54 3VMREF REF1/MultSel1 V_{DD}3.3V **[**] 4 53 GND XIN [52 SPREAD 5 XOUT [51 HCLK(1) GND [] 7 50 HCLK(1) PCI0 [49 V_{DD}3.3V 8 PCI1 ¶ 9 48 HCLK(2) V_{DD}3.3V **1** 10 47 HCLK(2) PCI2 [46 GND 11 PCI3 **∏** 12 45 | HCLK(3) GND **1** 13 44 HCLK(3) PCI4 [14 43 V_{DD}3.3V PCI5 **1** 15 42 HCLK(4) V_{DD}3.3V **1** 16 41 HCLK(4) PCI6 [17 40 GND 39 I_REF PCI7 **1** 18 GND **1** 19 38 V_{DD}3.3V PCI8 [20 37 | GND PCI9 **1** 21 36 V_{DD}3.3V V_{DD}3.3V **∏** 22 35 3V66(0) SEL100/133 [23 34 3V66(1) GND [33 **∏** GND 32 \ GND 3V48(0)/SeIA [25 26 31 **1** 3V66(2) 3V48(1)/SeIB [27 30 3V66(3) V_{DD}3.3V [28 29 V_{DD}3.3V PWRDWN [

DL PACKAGE (TOP VIEW)

All output frequencies are generated from a 14.318-MHz crystal input. A reference clock input can be provided at the XIN input instead of a crystal. Two phase-locked loops (PLLs) are used to generate the host frequencies and the 48-MHz clock frequencies. On-chip loop filters and internal feedback eliminate the need for external components. The host, PCI clock and 48-MHz clock outputs provide low-skew/low-jitter clock signals for reliable clock operation. All outputs have 3-state capability, which can be selected using control inputs SEL133, SelA and SelB.

The outputs are either differential host clock or 3.3-V single-ended CMOS buffers. When PWRDWN is set to high, the device operates in normal mode. When PWRDWN is set low, the device transitions to a power-down mode in which HCLK is driven at 2×I_{RFF}, HCLK is not driven, and all others are set low.



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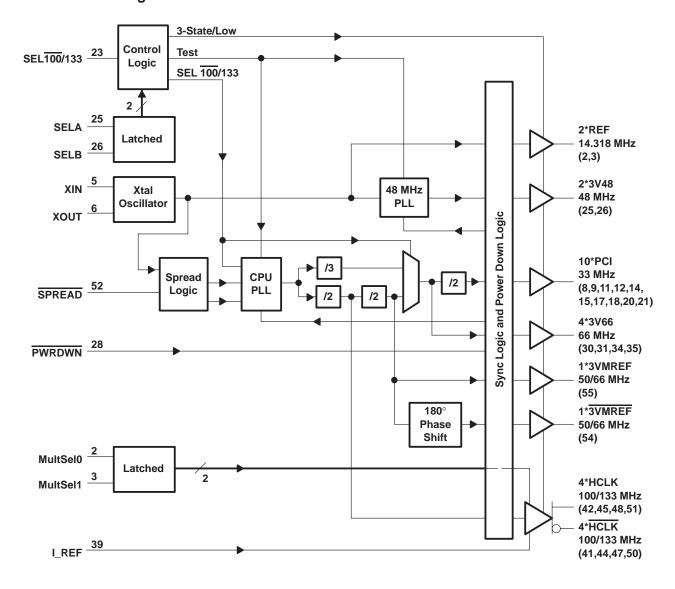
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description (continued)

The HOST bus operates at 100 MHz or 133 MHz. The MREF bus operates at 50 MHz or 66 MHz. Output frequency selection is accomplished with corresponding setting for SEL100/133 control input. The PCI bus frequency is fixed to 33 MHz.

Since the CDC930 is based on PLL circuitry, it requires a stabilization time to achieve phase-lock of the PLL. This stabilization time is required following power up as well as changes to SEL inputs. With use of external reference clock, this signal must be fixed-frequency and fixed-phase prior stabilization time starts.

functional block diagram





Terminal Functions

TERMINAL			
NAME	NO.	1/0	DESCRIPTION
3V48(0)/SeIA	25	I/O	Dual function 3.3 V, Type 3, 48-MHz clock output that latches the state of SelA during power up
3V48(1)/SelB	26	I/O	Dual function 3.3 V, Type 3, 48-MHz clock output that latches the state of SelB during power up
3V66[0-3]	30, 31, 34, 35	0	3.3 V, Type 5, 66-MHz clock outputs
3VMREF	55	0	3.3 V, Type 5, 50/66-MHz memory clock output
3VMREF	54	0	3.3 V, Type 5, 50/66-MHz memory clock output (180° out of phase with 3VMREF)
GND	1, 7, 13, 19, 24, 32, 33, 37, 40, 46, 53		Ground for core and HCLK/HCLK, 3VMREF/3VMREF, 3V48, 3V66 and PCI outputs
HCLK[1-4]	42, 45, 48, 51	0	Type X1, host clock outputs
HCLK[1-4]	41, 44, 47, 50	0	Type X1, host complementary clock outputs
I_REF	39	Special	Current reference pin for the host clock pairs. I_REF uses a fixed precision resistor tied to ground to establish the appropriate current.
PCI[0-9]	8, 9, 11, 12, 14, 15, 17, 18, 20, 21	0	3.3 V, Type 5, 33-MHz PCI clock outputs
PWRDWN	28	I	Power down for complete device with HOST at 2×I _{REF} , HCLK not driven and all other outputs forced low.
REF0/MultSel0	2	I/O	Dual function 3.3 V, Type 3, 14.318-MHz reference clock output. The state of MultSel0 is latched during power up. MultSel0 configures the I_{OH} amplitude (and thus the V_{OH} swing amplitude) of the HCLK pair outputs.
REF1/MultSel1	3	I/O	Dual function 3.3 V, Type 3, 14.318-MHz reference clock output. The state of MultSel1 is latched during power up. MultSel1 configures the I_{OH} amplitude (and thus the V_{OH} swing amplitude) of the HCLK pair outputs.
SEL100/133	23	ı	Active low LVTTL level logic select. SEL100/133 is used for enabling 100/133 MHz. Low=100 MHz, high=133 MHz
SPREAD	52	I	LVTTL level logic select. SPREAD pin enables/disables the spread spectrum for the HCLK/HCLK, 3VMREF/3VMREF, 3V66 and PCI outputs.
V _{DD} 3.3V	4, 10, 16, 22, 27, 29, 36, 38, 43, 49, 56	I	3.3-V power for core and the HCLK/HCLK, 3VMREF/3VMREF, 3V48, 3V66, and PCI outputs.
XIN	5	I	Crystal input – 14.318 MHz
XOUT	6	0	Crystal output – 14.318 MHz



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Function Tables

SELECT FUNCTIONS

INP	PUTS			FUNCTION					
SEL100/133	SelA	SelB	HOST, HCLK	3VMREF, 3VMREF	PCI	3V66	3V48	REF	FUNCTION
0	0	0	100 MHz	50 MHz	33 MHz	66 MHz	48 MHz	14.318 MHz	Active 100 MHz
0	1	1	Hi-Z	Hi-Z	Hi-Z	Hi-Z	Hi-Z	Hi-Z	All outputs 3-stated
1	0	0	133 MHz	66 MHz	33 MHz	66 MHz	48 MHz	14.318 MHz	Active 133 MHz
1	1	1	TCLK/2	TCLK/4	TCLK/8	TCLK/4	TCLK/2	TCLK	Test Mode

ENABLE FUNCTION

INPUT	OUTPUTS										
SEL100/133	HCLK	HCLK	3VMREF, 3VMREF	PCI	3V66	3V48	REF				
0	2×I _{REF}	Not driven	L	L	L	L	L				
1	On	On	On	On	On	On	On				

SPREAD SPECTRUM FUNCTION

INPUT		OUTPUTS
0		Spread spectrum clocking active, -0.6% at HCLK/HCLK, 3VMREF/3VMREF, 3V66, PCI
SPREAD 1		Spread spectrum clocking nonactive

OUTPUT BUFFER SPECIFICATIONS

BUFFER NAME	V _{DD} RANGE (V)	IMPEDANCE (Ω)	BUFFER TYPE
3V48, REF	3.135 – 3.465	20–60	TYPE 3
PCI, 3V66	3.135 – 3.465	12–65	TYPE 5
3VMREF/3VMREF	3.135 – 3.465	12–55	TYPE 5
HCLK/HCLK			TYPE X1

OUTPUT BUFFER SPECIFICATIONS

INPUTS		BOARD TARGET	REFERENCE R,	OUTPUT CURRENT	V _{OH} AT Z
MultSel0	MultSel1	TRACE/TERM Z	$I_{REF} = VDD/3 \times R_r$)	OUTFUT CORRENT	IREF = 2.32 mA
0	0	60 Ω	R _r = 475 1%, I _{REF} = 2.32 mA	I _{OH} = 5×I _{REF}	0.71 V at 60 Ω
0	0	50 Ω	$R_r = 475 1\%, I_{REF} = 2.32 mA$	I _{OH} = 5×I _{REF}	0.59 V at 50 Ω
0	1	60 Ω	$R_r = 475 1\%, I_{REF} = 2.32 mA$	I _{OH} = 6×I _{REF}	0.85 V at 60 Ω
0	1	50 Ω	R _r = 475 1%, I _{REF} = 2.32 mA	I _{OH} = 6×I _{REF}	0.71 V at 50 Ω
1	0	60 Ω	$R_r = 475 1\%$, $I_{REF} = 2.32 mA$	IOH = 4×IREF	0.56 V at 60 Ω
1	0	50 Ω	$R_r = 475 1\%$, $I_{REF} = 2.32 mA$	IOH = 4×IREF	0.47 V at 50 Ω
1	1	60 Ω	$R_r = 475 1\%$, $I_{REF} = 2.32 mA$	I _{OH} = 7×I _{REF}	0.99 V at 60 Ω
1	1	50 Ω	$R_r = 475 1\%, I_{REF} = 2.32 mA$	I _{OH} = 7×I _{REF}	0.82 V at 50 Ω

NOTE: The entries in **boldface** are the primary system configurations of interest. The outputs should be optimized for these configurations



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absolute maximum ratings over operating free-air temperature (unless otherwise noted)†

Supply voltage range, V _{DD}	
Input voltage range, V _I (see Note 1)	0.5 V to V _{DD} + 0.5 V
Voltage range applied to any output in the high-impedance state	or power-off state,
V _O (see Note 1)	0.5 V to V _{DD} + 0.5 V
Current into any output in the low state, IO	2 × rated I _{OL}
Input clamp current, I _{IK} (V _I < 0)	
$(V_I < V_{DD})$	18 mA
Output clamp current , I _{OK} (V _O < 0)	
$(V_O < V_{DD})$	50 mA
Package thermal impedance, θ _{JA} (see Note 2)	
Maximum power dissipation at $T_A = 55^{\circ}$ C (in still air) (see Note 3)) 1.3 W
Operating free-air temperature range, T _A	
Storage temperature range, T _{Stq}	
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
 - 2. The package thermal impedance is calculated in accordance with EIA/JEDEC Std JESD51, except for the through-hole packages, which use a trace length of zero. The absolute maximum power dissipation allowed at T_A = 55°C (in still air) is 1.3 W.
 - 3. The maximum package power dissipation is calculated using a junction temperature of 1505C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002.

DISSIPATION RATING TABLE

PACKAGE	$T_{\mbox{A}} \le 25^{\circ}\mbox{C}$ POWER RATING	DERATING FACTOR‡ ABOVE T _A = 25°C	T _A = 70°C POWER RATING	T _A = 85°C POWER RATING
DL	1558.6 mW	12.468 mW/°C	997.5 mW	810.52 mW

[‡] This is the inverse of the traditional junction-to-case thermal resistance (R_θJA) and uses a board-mounted device at 74°C/W.



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recommended operating conditions (see Note 2)

		MIN	иом†	MAX	UNIT	
Supply voltage, V _{DD}				3.465	V	
High-level input voltage, V _{IH}				V _{DD} + 0.3 V	V	
Low-level input voltage, V _{IL}		GND – 0.3 V		0.8	V	
Input voltage, V _I		0		V_{DD}	V	
High-level input voltage, V _{IL} Low-level input voltage, V _{IL} Input voltage, V _I High-level output current, I _{OH} Low-level output current, I _{OL} Reference frequency, f _(XIN) ‡ Crystal frequency, f _(XTAL) §	HCLK/HCLK			-20		
	3VMREF/3VMREF			-15	mA	
	48MHz, REFx			-16	IIIA	
	PCIx, 3V66x			-15		
	HCLK/HCLK			5	μА	
High-level input voltage, V _{IL} Low-level input voltage, V _{IL} Input voltage, V _I High-level output current, I _{OH} Low-level output current, I _{OL} Reference frequency, f _(XIN) ‡ Crystal frequency, f _(XTAL) §	3VMREF/3VMREF			10		
Low-level output current, IOL	48MHz, REFx			10	mA	
igh-level input voltage, V _{IL} pw-level input voltage, V _{IL} put voltage, V _I igh-level output current, I _{OH} pw-level output current, I _{OL} eference frequency, f _(XIN) ‡ rystal frequency, f _(XTAL) §	PCIx, 3V66x			10		
Reference frequency, f(XIN) [‡]	Test mode		14		MHz	
Crystal frequency, f(XTAL)§	Normal mode	13.8	14.318	14.8	MHz	
Operating free-air temperature, TA		0		85	°C	

[†] All nominal values are measured at their respective nominal V_{DD} values.

5. V_{IH} , V_{IL} : All input levels referenced to $V_{DD} = 3.30 \text{ V}$.



[‡] Reference frequency is a test clock driven on the XIN input during the device test mode and normal mode. In test mode, XIN can be driven externally up to $f_{(XIN)} = 16$ MHz. If XIN is driven externally, XOUT is floating. § This is a series fundamental crystal with $f_O = 14.31818$ MHz. NOTES: 4. Unused inputs must be held high or low to prevent them from floating.

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electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

	PARAMETER		TEST C	CONDITIONS	MIN TYPT	MAX	UNIT
VIK	Input clamp voltage		$V_{DD} = 3.135 V$,	I _I = -18 mA		-1.2	V
R _I	Input resistance	XIN-XOUT	$V_{DD} = 3.465 V,$	$V_{I} = V_{DD} - 0.5 V$	100		kΩ
		XOUT	$V_{DD} = 3.135 V,$	$V_{I} = V_{DD} - 0.5 V$		50	mA
Iн	High-level input current	MultSel0, MultSel1, SelA, SelB	V _{DD} = 3.465 V,	$V_I = V_{DD}$		10	μА
		SEL100/133 SPREAD, PWRDWN	V _{DD} = 3.465 V,	$V_I = V_{DD}$		5	μΑ
		XOUT	$V_{DD} = 3.135 V$,	VO = 0 V		-5	mA
	l and land in the arms of	MultSel0, MultSel1, SelA, SelB,	V _{DD} = 3.465 V,	V _I = GND		-10	μΑ
¹IL	Low-level input current	SEL100/133 SPREAD, PWRDWN	V _{DD} = 3.465 V,	V _I = GND		-5	μΑ
		I_REF	$V_{DD} = 3.465 V,$	R _r = 221		-5.5	mA
loz	High-impedance-state outp	out current	V _{DD} = 3.465 V	$\begin{array}{c} \text{SEL}\underline{A}, \text{SELB} = H,\\ \text{SEL}\overline{100}/133 \text{H} \rightarrow \text{L}\\ \underline{V_O} = V_{\mbox{\scriptsize DD}} \text{or GND}\\ \mbox{PWRDWN} = \mbox{H} \end{array}$		±10	μΑ
I _{DD(Z)}	High-impedance-state sup	ply current	V _{DD} = 3.465 V	$\begin{array}{c} \text{SELA, SELB = H,} \\ \text{SEL} \overline{100} / 133 \text{ H} \rightarrow \text{L} \\ \hline \text{PWRDWN = H} \end{array}$		40	mA
I _{DD(PD)}	PWRDWN state supply cu	rrent	$V_{DD} = 3.465 V,$	PWRDWN = L		30	mA
I _{DD}	Dynamic supply current		V _{DD} = 3.465 V			250	mA
Cl	Input capacitance‡		$V_{DD} = 3.3 \text{ V},$	$V_I = V_{DD}$ or GND	2	5	pF
C _(XTAL)	Crystal terminal capacitane	ce	V _{DD} = 3.3 V,	V _I = 0.3 V	18		pF

[†] All typical values are measured at their respective nominal V_{DD} values.



[‡] These parameters are ensured by design and lab characterization, not 100% production tested.

 $^{{\}sf Control\ SELx,\ \overline{PWRDWN},\ \overline{SPREAD}\ threshold\ levels\ d\underline{uring}\ FUNC\ w/c\ level\ tests.}$

C_L = MAX = 5 pF, R_S = 33.2 Ω , R_p = 49.9 Ω at HCLK/HCLK (Type X1) C_L = MAX = 20 pF, R_L = 500 Ω at 48 MHz, REF (Type 3) C_L = MAX = 30 pF, R_L = 500 Ω at PCIx, 3V66, 3VMREF, 3VMREF (Type 5)

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electrical characteristics over recommended operating free-air temperature range (unless otherwise noted) (continued)

HCLK/HCLK (Type X1)

	PARAMETER		TEST CONDITIONS		MIN	TYP†	MAX	UNIT
		$I_{ref} = 2.32 \text{ mA} \times 4$	V _{DD} = 3.135 V		-8.1			mA
		ref = 2.32 mA × 4	V _{DD} = 3.465 V	_			-10.5	IIIA
		I _{ref} = 2.32 mA × 5	V _{DD} = 3.135 V		-10.1			mA
		ref = 2.32 mA × 3	V _{DD} = 3.465 V	V_{OH} at $Z = 50 \Omega$			-13.1	ША
ЮН	High-level output current	1 t = 2.22 mA v 6	V _{DD} = 3.135 V	VOH at 2 = 30 32	-12.1			mA
		$I_{ref} = 2.32 \text{ mA} \times 6$	V _{DD} = 3.465 V				-15.7	IIIA
		I _{ref} = 2.32 mA × 7	V _{DD} = 3.135 V		-14.1			mA
		ref = 2.32 mA × 7	V _{DD} = 3.465 V				-18.4	IIIA
СО	Output capacitance‡	$V_O = V_{DD}$ or GND				3.5		pF

[†] All typical values are measured at their respective nominal V_{DD} values.

48MHz, REFx (Type 3), $C_L = 20$ pF, $R_L = 500 \Omega$

	PARAMETER	TEST CO	NDITIONS	MIN	TYP†	MAX	UNIT
Vон	High-level output voltage	V _{DD} = min to max,	I _{OH} = -1 mA	VDD – 0.1 V			V
0		V _{DD} = 3.135 V,	I _{OH} = -14 mA	2.4			
V/01	Low-level output voltage	V _{DD} = min to max,	I _{OL} = 1 mA			0.1	V
VOL	Low-level output voltage	$V_{DD} = 3.135 \text{ V},$	$I_{OL} = 9 \text{ mA}$			0.4	V
		$V_{DD} = 3.135 \text{ V},$	V _O = 1 V	-29			
loh	High-level output current	$V_{DD} = 3.3 \text{ V},$	V _O = 1.65 V		-41		mA
		$V_{DD} = 3.465 \text{ V},$	V _O = 3.135 V			-23	
		$V_{DD} = 3.135 \text{ V},$	V _O = 1.95 V	29			
IOL	Low-level output current	$V_{DD} = 3.3 \text{ V},$	V _O = 1.65 V		53		mA
		V _{DD} = 3.465 V,	V _O = 0.4 V			27	
СО	Output capacitance [‡]	V _{DD} = 3.3 V,	$V_O = V_{DD}$ or GND	2		5	pF

[†] All typical values are measured at their respective nominal VDD values.

PCIx, 3V66x, MREF/MREF (Type 5), $C_1 = 20$ pF, $R_1 = 500 \Omega$

PARAMETER		TEST CO	TEST CONDITIONS		TYP [†]	MAX	UNIT
Vон	High-level output voltage	V _{DD} = min to max,	I _{OH} = -1 mA	VDD – 0.1 V			V
011		$V_{DD} = 3.135 V,$	I _{OH} = -18 mA	2.4			
V/01	Low lovel output voltage	V _{DD} = min to max,	I _{OL} = 1 mA			0.1	V
VOL	Low-level output voltage	$V_{DD} = 3.135 V,$	$I_{OL} = 12 \text{ mA}$			0.4	V
		$V_{DD} = 3.135 V,$	V _O = 1 V	-33			
loh	High-level output current	$V_{DD} = 3.3 V,$	V _O = 1.65 V		-53		mA
		$V_{DD} = 3.465 V,$	V _O = 3.135 V			-33	
		$V_{DD} = 3.135 V,$	V _O = 1.95 V	30			
I_{OL}	Low-level output current	$V_{DD} = 3.3 V,$	V _O = 1.65 V		70		mA
		$V_{DD} = 3.465 V,$	$V_0 = 0.4 \text{ V}$			38	
СО	Output capacitance [‡]	$V_{DD} = 3.3 V,$	$V_O = V_{DD}$ or GND	2		5	pF

[†] All typical values are measured at their respective nominal V_{DD} values.

[‡]These parameters are ensured by design and lab characterization, not 100% production tested.



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switching characteristics, V_{DD} = MIN to MAX, T_A = 0°C to 85°C

	PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	MIN	TYP	MAX	UNIT						
vover	Overshoot [‡]			HCLK/HCLK 0.7 V ampli-			V _{OH} +200	mV						
Vunder	Undershoot [‡]			tude			V _{OL} -200	mv						
vover	Overshoot [‡]			Other clocks, C _L = Worst	GND-0.7			V						
Vunder	Undershoot [‡]		case				V _{DD} +0.7	v						
t _{PZL}	Output enable time to low level			f(HCL) = 100 or 133 MHz, SELA, SELB = H,			100	ns						
^t PZH	Output enable time to high level	SEL100/133	HCLK/	SEL $\overline{100}/133 L \rightarrow H$, R _{ref} = 475 Ω			100	ns						
^t PHZ	Output disable time from high level	SEL100/133	HCLK	HCLK	f(HCL) = 100 or 133 MHz, SELA, SELB = H,			10	ns					
^t PLZ	Output disable time from low level			SEL $\overline{100}/133 \text{ H} \rightarrow \text{L},$ R _{ref} = 475 Ω			10	ns						
^t PZL	Output enable time to low level			f(HCL) = 100 or 133 MHz, SELA, SELB = H,			10	ns						
^t PZH	Output enable time to high level	SEL100/133	REF, 3V48 3VMREF,	,	,	REF, 3V48 3VMREF,	,	· '	· · · · · · · · · · · · · · · · · · ·	SEL $\overline{100}$ /133 L \rightarrow H, R _{ref} = 475 Ω			10	ns
^t PHZ	Output disable time from high level	SEL 100/133	3VMREF, 3V66, PCI	OVANDEE.	OVANDEE	f(HCL) = 100 or 133 MHz, SELA, SELB = H,	10	ns						
tPLZ	Output disable time from low level			SEL $\overline{100}/133 \text{ H} \rightarrow \text{L},$ R _{ref} = 475 Ω	→ L,		10	ns						
t _{stab}	Stabilization time†			After power up			3	ms						

[†] Stabilization time is the time required for the integrated PLL circuit to obtain phase lock of its feedback signal to its reference signal. In order for phase lock to be obtained, a fixed-frequency, fixed-phase reference signal must be present a XIN. Until phase lock is obtained, the specifications for propagation delay and skew parameters given in the switching characteristics tables are not applicable. Stabilization time is defined as the time from when V_{DD} achieves its nominal operating level until the output frequency is stable and operating within specification.

HCLK/ $\overline{\text{HCLK}}$ (Type X1) C_L = 2 pF, R_L > 500 k Ω

	PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	MIN	TYP M	λX	UNIT
	LICLIC algorithms with 4th			f(HCLK) = 100 MHz	10	10).2	no
t _C	HCLK clock period [†]			f(HCLK) = 133 MHz	7.5	7.	65	ns
^t jit(cc)	Cycle to cycle jitter			f(HCLK = 100 or 133 MHz		2	00	ps
t _{dc}	Duty cycle			f(HCLK) = 100 or 133 MHz crossing point	45%	55	5%	
t _{sk(o)}	HCLK bus skew	HCLKx	HCLKx	f(HCLK) = 100 or 133 MHz crossing point		1	50	ps
	Pulse duration width			f(HCLK = 100 MHz	4.41			no
t _W	Pulse duration width			f(HCLK = 133 MHz	3.29			ns
t _r	Rise time‡			V _O = 0.14 V to 0.56 V	175	7	00	ps
t _f	Fall time‡	0.7 V amplitude		V _O = 0.14 V to 0.56 V	175	7	00	ps
t _r , t _f	Rise and fall time matching [‡]	ampillade		$2 \times (t_{\Gamma} - t_{f})/(t_{\Gamma} + t_{f})$		20	%	
v _{cross}	Cross point voltages‡	0.7 V amplitude		f(HCLK) = 100 or 133 MHz HCLK and HCLK	40% VOH		5% DH	V

[†] The average over any 1-μs period of time is greater than the minimum specified period.



[‡] These parameters are ensured by design and lab characterization, not 100% production tested.

[‡] These parameters are ensured by design and lab characterization, not 100% production tested.

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switching characteristics, $V_{DD} = 3.135 \text{ V}$ to 3.465 V, $T_A = 0^{\circ}\text{C}$ to 85°C (continued)

3VMREF/3VMREF (Type 5) C_L = 30 pF, R_L = 500 Ω

	PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	MIN	TYP	MAX	UNIT
	3VMREF/3VMREF clock			f(3VMREF/3VMREF) = 50 MHz	20		20.4	ns
t _C	period†			f(3VMREF/3VMREF) = 66 MHz	15		15.3	ns
^t jit(cc)	Cycle to cycle jitter			f(3VMREF/3VMREF) = 66 MHz, f(HCLK) = 100 or 133 MHz, VDD = 3.3 V, Measured at 1.5 V			250	ps
t _{dc}	Duty cycle			f(3VMREF/3VMREF) = 66 MHz	45%		55%	
t _{sk(o)}	3VMREF/3VMREF output skew	3VMREF/ 3VMREF	3VMREF/ 3VMREF	f(3VMREF/3VMREF) = 66 MHz, f(HCLK) = 100 or 133 MHz, VDD = 3.3 V, Measured at 1.5 V			250	ps
t(off)	3VMREF/3VMREF clock to PCI offset	3VMREF/ 3VMREF	PCIx	f(3VMREF/3VMREF) = 66 MHz, Measured points at 1.5 V, Measured at rising edges			3	ns
t _r	Rise time			V _O = 0.4 V to 2.4 V	0.5		2	ns
tf	Fall time			V _O = 0.4 V to 2.4 V	0.5		2	ns

[†] The average over any 1-µs period of time is greater than the minimum specified period.

3V66 (Type 5, No SSC), C_L = 30 pF, R_L = 500 Ω

	PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _C	3V66 clock period [†]			f(3V66)= 66 MHz		15.03		ns
^t jit(cc)	Cycle to cycle jitter			f(3V66) = 66 MHz, f(HCLK) = 100 or 133 MHz, VDD = 3.3 V, Measured at 1.5 V			300	ps
t _{dc}	Duty cycle			f(3V66) = 66 MHz	45%		55%	
^t sk(o)	3V66 output skew	3V66x	3V66x	f(3V66) = 66 MHz, f(HCLK) = 100 or 133 MHz, VDD = 3.3 V, Measured at 1.5 V			250	ps
^t (off)	3V66 clock to PCI	3V66x	PCIx	f(3V66) = 66 MHz, Measured points at 1.5 V, Measured at rising edges	1.5		3.5	ns
t _r	Rise time			V _O = 0.4 V to 2.4 V	0.5		2	ns
t _f	Fall time			V _O = 0.4 V to 2.4 V	0.5		2	ns

[†] The average over any 1-µs period of time is greater than the minimum specified period.

PCI (Type 5), C_L = 30 pF, R_L = 500 Ω

	PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _C	PCI clock period [†]			f _(PCI) = 33.3 MHz		30.06		ns
tjit(cc)	Cycle to cycle jitter			f(HCLK) = 100 or 133 MHz			500	ps
t _{dc}	Duty cycle			f _(PCI) = 33.3 MHz	45%		55%	
t _{sk(o)}	PCI output skew	PCIx	PCIx	f(PCI) = 33.3 MHz			500	ps
t _r	Rise time			V _O = 0.4 V to 2.4 V	0.5		2	ns
tf	Fall time			V _O = 0.4 V to 2.4 V	0.5		2	ns

[†] The average over any $1-\mu s$ period of time is greater than the minimum specified period.



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switching characteristics, V_{DD} = 3.135 V to 3.465 V, T_A = 0°C to 85°C (continued)

3V48 (Type 3), C_L = 20 pF, R_L = 500 Ω

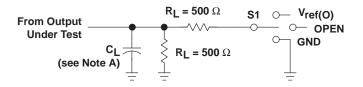
	PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _C	3V48 clock period†			f(3V48)= 48 MHz		15.03		ns
^t jit(cc)	Cycle to cycle jitter			f _(3V48) = 48 MHz, f _(HCLK) = 100 or 133 MHz, V _{DD} = 3.3 V, Measured at 1.5 V			350	ps
t _{dc}	Duty cycle			f(3V48) = 48 MHz	45%		55%	
tsk(o)	3V48 output skew	3V48x	3V48x	$f_{(3V48)} = 48 \text{ MHz},$ $f_{(HCLK)} = 100 \text{ or } 133 \text{ MHz},$ $V_{DD} = 3.3 \text{ V}, \text{ Measured at } 1.5 \text{ V}$			250	ps
t(off)	3V48 clock to PCI	3V48x	PCIx	f(3V48) = 48 MHz, Measured points at 1.5 V, Measured at rising edges	1.5		3.5	ns
t _r	Rise time			V _O = 0.4 V to 2.4 V	1		4	ns
t _f	Fall time			V _O = 0.4 V to 2.4 V	1		4	ns

[†] The average over any 1–µs period of time is greater than the minimum specified period.

REF (Type 3), C_L = 20 pF, R_L = 500 Ω

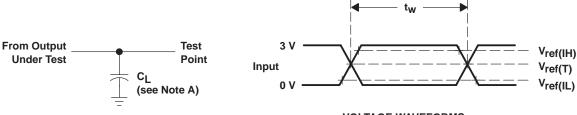
	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _C	REF clock period†	f(REF)= 14.318 MHz		69.84		ns
tjit(cc)	Cycle to cycle jitter	f(HCLK) = 100 or 133 MHz			1	ps
t _{dc}	Duty cycle	f(REF) = 14.318 MHz	52%		62%	
t _r	Rise time	$V_0 = 0.4 \text{ V to } 2.4 \text{ V}$	1		4	ns
tf	Fall time	V _O = 0.4 V to 2.4 V	1		4	ns

[†] The average over any 1-μs period of time is greater than the minimum specified period.



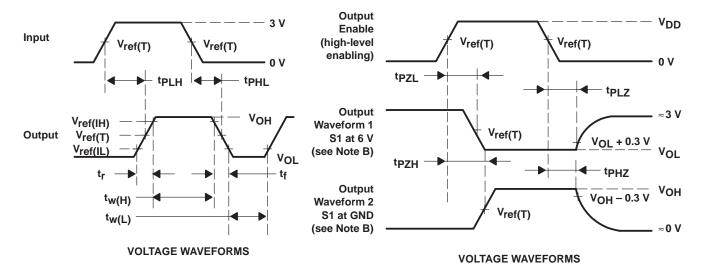
TEST	S1
tPLH/tPHL	Open
tPLZ/tPZL	V _{ref} (OFF)
tPHZ/tPZH	GND

LOAD CIRCUIT of single-ended outputs for tpd and tsk



LOAD CIRCUIT of single-ended outputs for tr and tf





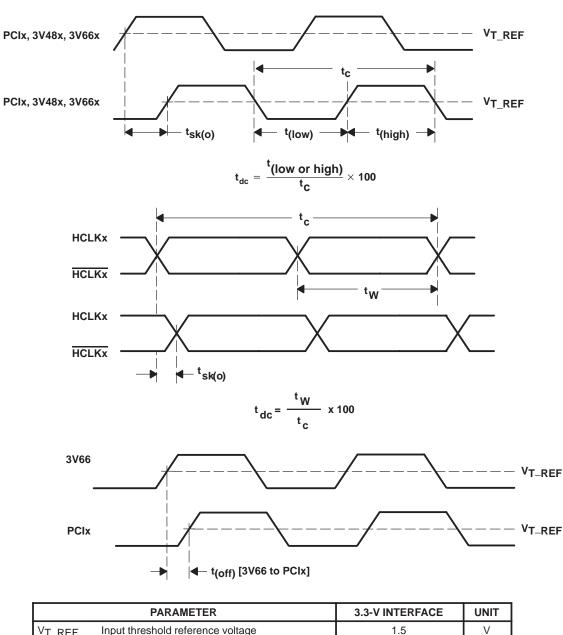
NOTES: A. CL includes probe and jig capacitance. CL = 2 pF (HCLK, HCLK), CL = 20 pF (48MHZ, REF), CL = 30 pF (PCIx, 3VMREF, 3V66).

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 14.318 MHz, $Z_O = 50 \Omega$, $t_r \leq 2.5 \text{ ns}$, $t_f \le 2.5 \text{ ns.}$
- D. The outputs are measured one at a time with one transition per measurement.

	PARAMETER	3.3-V INTERFACE	2.5-V INTERFACE	UNIT
V _{ref(IH)}	High-level reference voltage	2.4	2	V
V _{ref(IL)}	Low-level reference voltage	0.4	0.4	V
V _{ref(T)}	Input threshold reference voltage	1.5	1.25	V
V _{ref} (OFF)	Off-state reference voltage	6	4.6	V

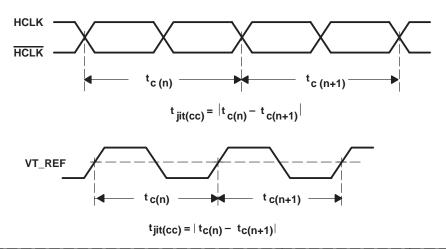
Figure 1. Load Circuit and Voltage Waveforms





	PARAMETER	3.3-V INTERFACE	UNIT
VT_REF	Input threshold reference voltage	1.5	V

Figure 2. Waveforms for Calculation of Output Skew, Duty Cycle, and Offset



	PARAMETER	3.3-V INTERFACE	UNIT
VT_REF	Input threshold reference voltage	1.5	V

Figure 3. Waveforms for Calculation of Cycle-Cycle Jitter

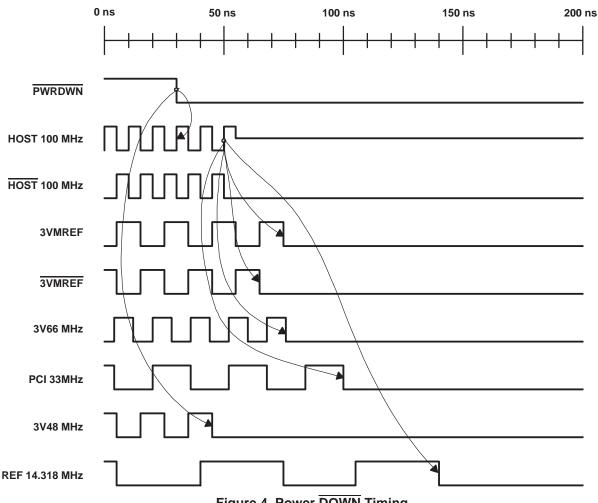
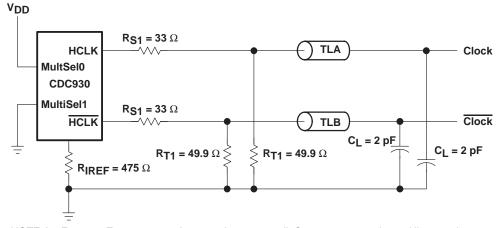


Figure 4. Power DOWN Timing



NOTE A: $Z_{(TLA)} = Z_{(TLB)} = 50 \Omega$, $L_{(TLA)} = L_{(TLB)} = 3.5$ ", C_L represents probe and jig capacitance.

Figure 5. Load Circuit for 0.7 V Amplitude HCLK/HCLK Bus



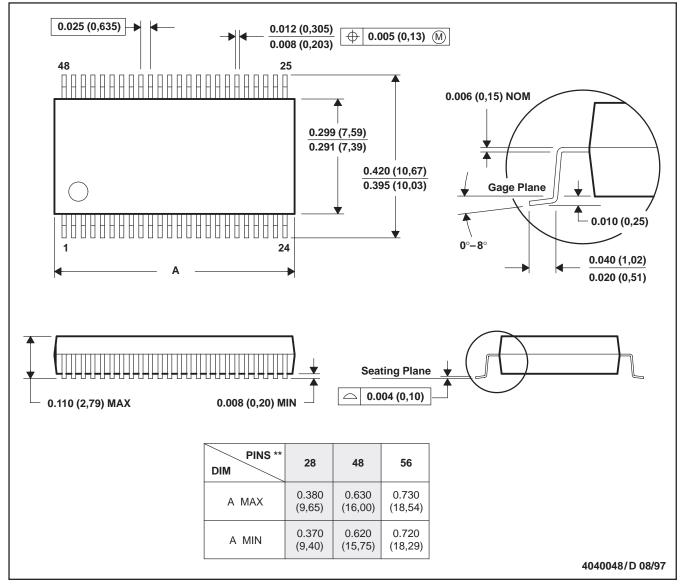
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MECHANICAL DATA

DL (R-PDSO-G**)

48-PIN SHOWN

PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
- D. Falls within JEDEC MO-118



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